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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
			Application Number	10/796,111-Conf. #2460	
			Filing Date	March 10, 2004	
			First Named Inventor	Dean A. Klein	
			Art Unit	2824	
			Examiner Name	P. M. Luu	
Sheet	1	of	1	Attorney Docket Number	M4065.0959/P959

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
PL	CA	Nature Publishing Group, Lankhorst et al, "Low-cost and nanoscale on-volatile memory concept for future silicon chips", pp. 347-352, 2005	
PL	CB	Institute of Physics Publishing, Ltd., Tugluoglu et al., "Temperature dependent barrier characteristics of Ag/p-SnSe Schottky diodes based on I-V-T measurements", pp.1092-1097, 2004, UK	
PL	CC	American Institute of Physics, Pattanayak et al, "Signature of silver phase percolation threshold in microscopically phase separated ternary Ge _{0.15} Se _{0.85-x} Ag _x (0 ≤ x ≤ 0.20) glasses", Journal of Applied Physics, pp. 013515-1 - 013515-4, 2004	

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Examiner Signature	P. M. Luu	Date Considered	10/16/05
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